MSKSEMI















ESD

TVS

TSS

MOV

GDT

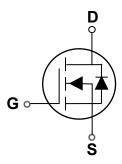
PLED

Broduct data sheet





SOT-23-3L



Features

- 20V, 6.5A, RDS(ON)=16mΩ@VGS=4.5V
- Improved dv/dt capability
- Fast switching
- Green Device Available

Applications

- Notebook
- Load Switch
- Hend-Held Instruments

BVDSS	RDSON	ID
20V	16mΩ	6.5A

Absolute Maximum Ratings Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	20	V
V _{GS}	Gate-Source Voltage	±12	V
	Drain Current – Continuous (T _C =250)	6.5	A
ID	Drain Current – Continuous (T _C =1000)	4.2	А
I _{DM}	Drain Current – Pulsed ¹	26.8	А
D	Power Dissipation (T _C =250)	1.56	W
P _D	Power Dissipation – Derate above 250	0.012	W/ C
T _{STG}	Storage Temperature Range	-55 to 150	С
TJ	Operating Junction Temperature Range	-55 to 150	С

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
Reja	Thermal Resistance Junction to ambient		80	c/ W



Off Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA				V
△BV _{DSS} /△T _J	BV _{DSS} Temperature Coefficient	Reference to 250 , I _D =1mA		0.02		V/ C
	Drain-Source Leakage Current	V _{DS} =20V , V _{GS} =0V , T _J =250			1	uA
IDSS		V _{DS} =16V , V _{GS} =0V , T _J =1250			10	uA
Igss	Gate-Source Leakage Current	V _{GS} =±10V , V _{DS} =0V			±100	nA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =4.5V , I _D =4A		16	22	mΩ	
NDS(ON) Static Drain-Source On-Nesistance	V _{GS} =2.5V , I _D =3A		18	24	11 52		
V _{GS(th)}	Gate Threshold Voltage	V -V 1 -250A		0.6	1.0	V	
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	V _{GS} =V _{DS} , I _D =250uA		2		mV/ C	
gfs	Forward Transconductance	V _{DS} =10V , I _S =4A		9.5		S	

Dynamic and switching Characteristics

Qg	Total Gate Charge ^{2, 3}			5.8	
Q_{gs}	Gate-Source Charge ^{2, 3}	V _{DS} =10V , V _{GS} =4.5V , I _D =4A		0.6	 nC
Q_{gd}	Gate-Drain Charge ^{2, 3}			2	
T _{d(on)}	Turn-On Delay Time ^{2,3}			5.0	
Tr	Rise Time ^{2,3}	V_{DD} =10V , V_{GS} =4.5V , R_{G} =25 Ω		14.4	 nS
$T_{d(off)}$	Turn-Off Delay Time ^{2,3}	I _D =1A		30.0	 113
T_f	Fall Time ^{2,3}			9.2	
Ciss	Input Capacitance			600	
Coss	Output Capacitance	V_{DS} =10V , V_{GS} =0V , F=1MHz		70	 pF
C _{rss}	Reverse Transfer Capacitance			45	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions		Тур.	Max.	Unit
Is	Continuous Source Current	\/-=\/-=0\/ Force Current			6.5	Α
I _{SM}	Pulsed Source Current	V _G =V _D =0V , Force Current			13	Α
V _{SD}	Diode Forward Voltage	V _{GS} =0V , I _S =1A , T _J =250			1.2	V

Note :

- 1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
- 2. The data tested by pulsed , pulse width \leq 300 us , duty cycle \leq 2%.
- 3. Essentially independent of operating temperature.



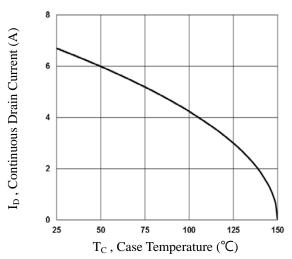


Fig.1 Continuous Drain Current vs. T_c

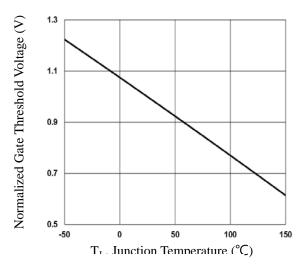


Fig.3 Normalized V_{th} vs. T_J

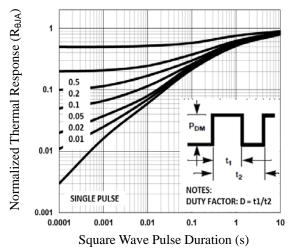


Fig.5 Normalized Transient Impedance

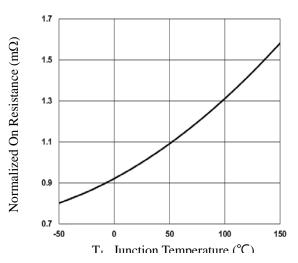


Fig.2 Normalized RDSON vs. T_J

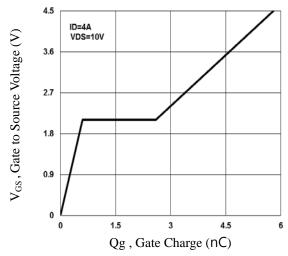


Fig.4 Gate Charge Waveform

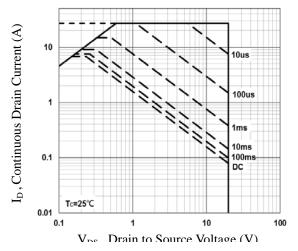
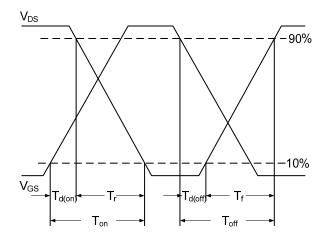


Fig.6 Maximum Safe Operation Area





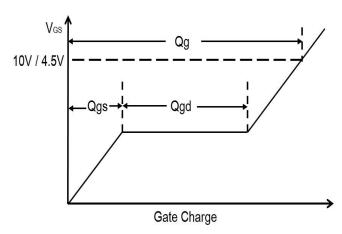
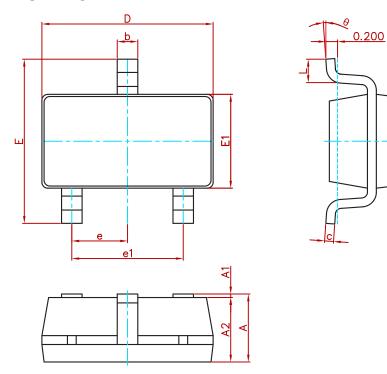


Fig.7 Switching Time Waveform

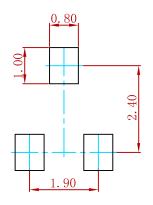
Fig.8 Gate Charge Waveform

PACKAGE MECHANICAL DATA



Symbol	Dimensions In	Dimensions In Millimeters		s In Inches
Symbol	Min.	Max.	Min.	Max.
Α	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
е	0.950(0.950(BSC)		(BSC)
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Suggested Pad Layout



- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
AO3416	SOT-23-3L	3000



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STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 IPS60R360PFD7SAKMA1
DMN2990UFB-7B SSM3K35CT,L3F IPLK60R1K0PFD7ATMA1 2N7002W-G MCAC30N06Y-TP IPWS65R035CFD7AXKSA1
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